

FEATURES

- Epitaxial planar die construction.
- Complementary NPN type available (MMBT4401).
- Also available in lead free version.
- Ideal for medium power amplification and switching.

SOT-23		
Dim	Min	Max
А	2.70	3.10
В	1.10	1.50
С	1.0 Typical	
D	0.4 Typical	
E	0.35	0.48
G	1.80	2.00
Н	0.02	0.1
J	0.1 Typical	
К	2.20	2.60
All Dimensions in mm		

APPLICATIONS

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• Ideal for medium power amplification and switching.

ORDERING INFORMATION

Type No.	Marking	Package Code
MMBT4403	2T	SOT-23

MAXIMUM RATING @ Ta=25°C unless otherwise specified

Symbol	Parameter	Value	UNIT
V _{CBO}	collector-base voltage	-40	V
V _{CEO}	collector-emitter voltage	-40	V
V _{EBO}	emitter-base voltage	-5	V
l _C	collector current (DC)	-0.6	А
P _C	Collector dissipation	0.35	W
R _{0JA}	Thermal Resistance, Junction to Ambient	357	°C/W
T _j ,T _{stg}	junction and storage temperature	-55 to +150	°C

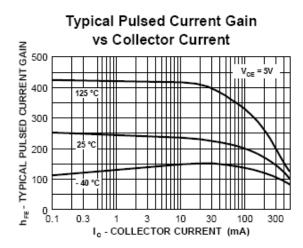


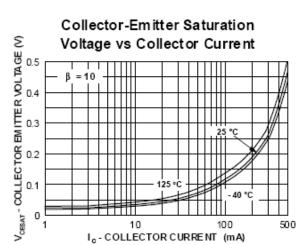
MMBT4403 PNP General Purpose Transistor

Symbol	Parameter	Test conditions	MIN.	MAX.	UNIT
V _{(BR)CBO}	Collector-base breakdown voltage	Ι _C =-100μΑ,Ι _E =0	-40		
V _{(BR)CEO}	Collector-emitter breakdown voltage	I _C =-1mA,I _B =0	-40		
V _{(BR)EBO}	Emitter-base breakdown voltage	Ι _E =-100μΑ,Ι _C =0	-5		
I _{CEX}	collector cut-off current	V _{CE} =-35V,V _{BE} =0.4V		-0.1	μA
I _{BL}	Base cut-off current	V _{CE} =-35V,V _{BE} =-0.4V		-0.1	μA
h _{FE}	DC current gain	$V_{CE} = -1V; I_C = -0.1mA$ $V_{CE} = -1V; I_C = -1mA$ $V_{CE} = -1V; I_C = -10mA$ $V_{CE} = -2V; I_C = -150mA$ $V_{CE} = -2V; I_C = -500mA$	30 60 100 100 20	300	
V _{CE(sat)}	collector-emitter saturation voltage	I _C = -150mA ,I _B = -15mA I _C = -500mA ,I _B = -50mA	-	-0.4 -0.75	V
V _{BE(sat)}	base-emitter saturation voltage	I _C = -150mA; I _B = -15mA I _C = -500mA; I _B = -50mA	-0.75	-0.95 -1.3	V
f _T	transition frequency	I _C = -20mA; V _{CE} = -10V; f =100MHz	200	-	MHz

ELECTRICAL CHARACTERISTICS @ Ta=25°C unless otherwise specified

TYPICAL CHARACTERISTICS @ Ta=25°C unless otherwise specified

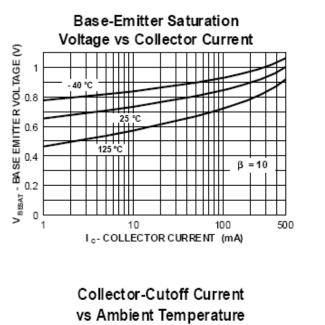


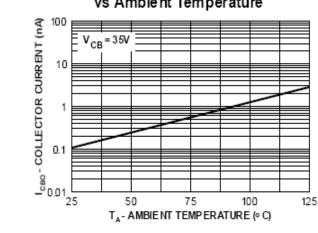


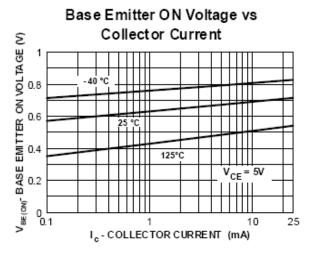


MMBT4403 PNP General Purpose Transistor

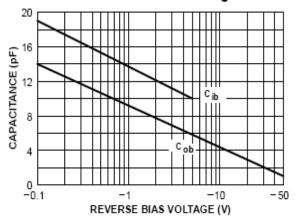
RoHS COMPLIANT

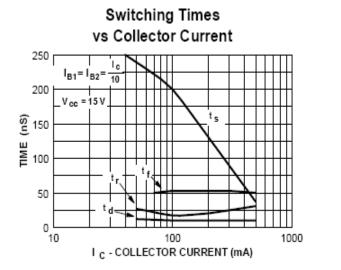




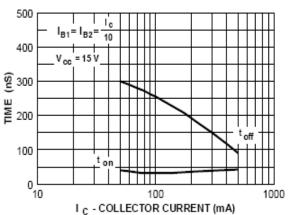


Input and Output Capacitance vs Reverse Bias Voltage





Turn On and Turn Off Times vs Collector Current



Device	Package	Shipping
MMBT4403	SOT-23	3000/Tape&Reel

http://www.lgesemi.com

mail:lge@lgesemi.com

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